



P-Channel 2.5-V (G-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)		
- 20	0.00775 at V _{GS} = - 4.5 V	- 14		
- 20	0.01225 at V _{GS} = - 2.5 V	- 11		

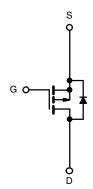
FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- Compliant to RoHS Directive 2002/95/EC

RoHS COMPLIANT HALOGEN FREE

APPLICATIONS

· Load Switch



P-Channel MOSFET

	SO-8	_	
S 1 S 2 S 3 G 4		8 7 6 5	D D D
'	Top View	_	

Ordering Information: Si4493DY-T1-E3 (Lead (Pb)-free)

Si4493DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS	Γ _A = 25 °C, unle	ss otherwise r	noted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 20		V
Gate-Source Voltage		V _{GS}	± 12		
Opation	T _A = 25 °C	- I _D	- 14	- 10	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		- 11	- 8	
Pulsed Drain Current		I _{DM}	- 50		Α
Continuous Source Current (Diode Conduction) ^a		I _S	- 2.7	- 1.36	
W	T _A = 25 °C	- P _D	3.0	1.5	W
Maximum Power Dissipation ^a	T _A = 70 °C		1.9	0.95	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Manifestore Longition to Applicated	t ≤ 10 s	- R _{thJA}	33	42	
Maximum Junction-to-Ambient ^a	Steady State		70	84	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	16	21	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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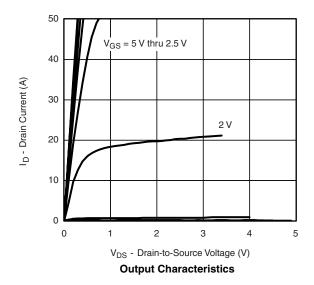
Parameter	Symbol	Test Conditions Min. Typ.		Max.	Unit	
Static					'	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 0.6		- 1.4	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 20 V, V _{GS} = 0 V	- 1 - 10		- 1	μΑ
		V _{DS} = - 20 V, V _{GS} = 0 V, T _J = 70 °C			- 10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 4.5 V	- 30			Α
Drain-Source On-State Resistance ^a	D	V _{GS} = - 4.5 V, I _D = - 14 A		0.0065	0.00775	0
	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 11 A		0.010	0.01225	Ω
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 14 A		60		S
Diode Forward Voltage ^a	V_{SD}	I _S = - 2.7 A, V _{GS} = 0 V		- 0.68	- 1.1	V
Dynamic ^b					•	
Total Gate Charge	Q_g			65	110	
Gate-Source Charge	Q_{gs}	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -14 \text{ A}$		14.5		nC
Gate-Drain Charge	Q_{gd}			21		
Turn-On Delay Time	t _{d(on)}			110	165	
Rise Time	t _r	V_{DD} = - 10 V, R_L = 10 Ω		150	225	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 1 A, V_{GEN} = - 4.5 V, R_g = 6 Ω		220	330	ns
Fall Time	t _f			140	210	
Gate Resistance	R_g			3.8		Ω
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 2.7 A, dl/dt = 100 A/μs		85	130	ns

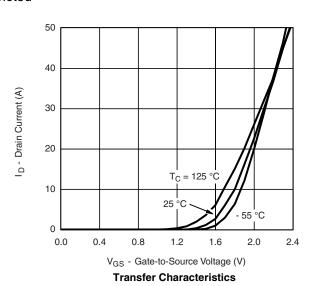
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



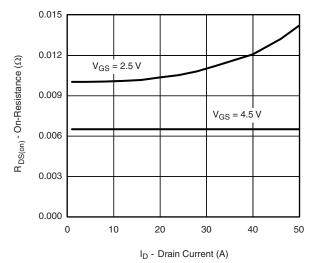




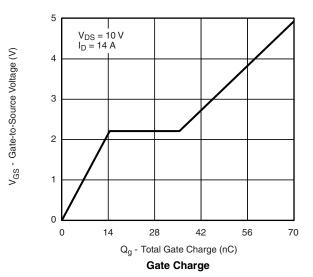


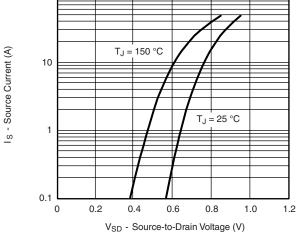


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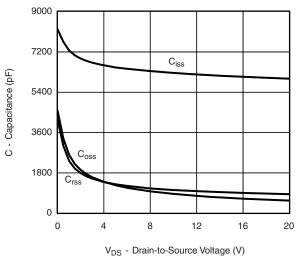


On-Resistance vs. Drain Current

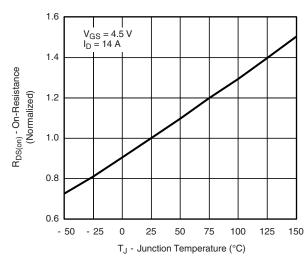




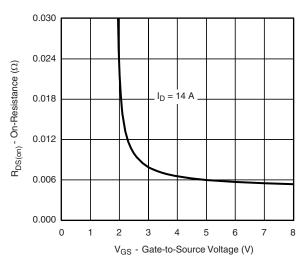
Source-Drain Diode Forward Voltage



Capacitance



On-Resistance vs. Junction Temperature



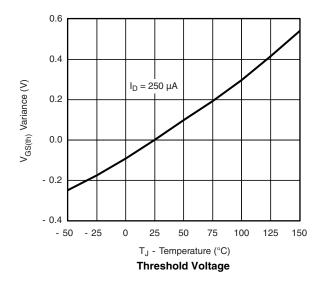
On-Resistance vs. Gate-to-Source Voltage

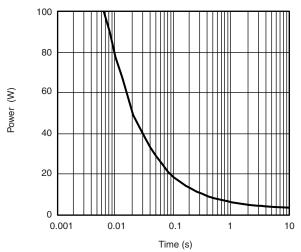
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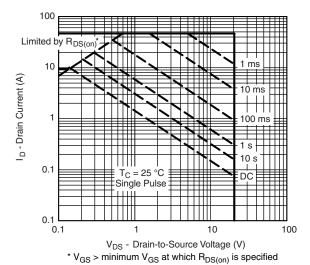
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

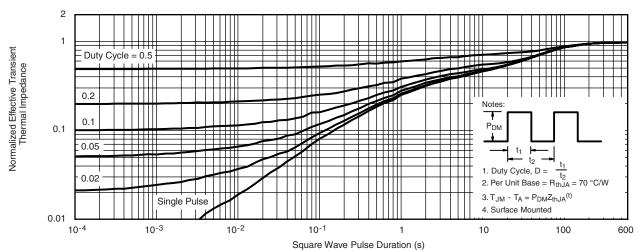




Single Pulse Power, Junction-to-Ambient



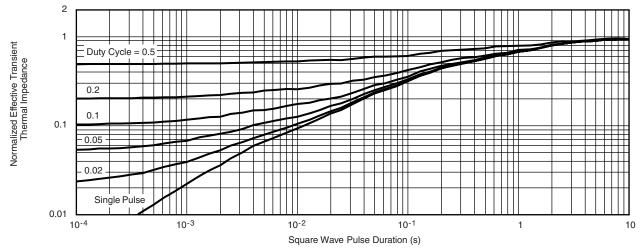
Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

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